

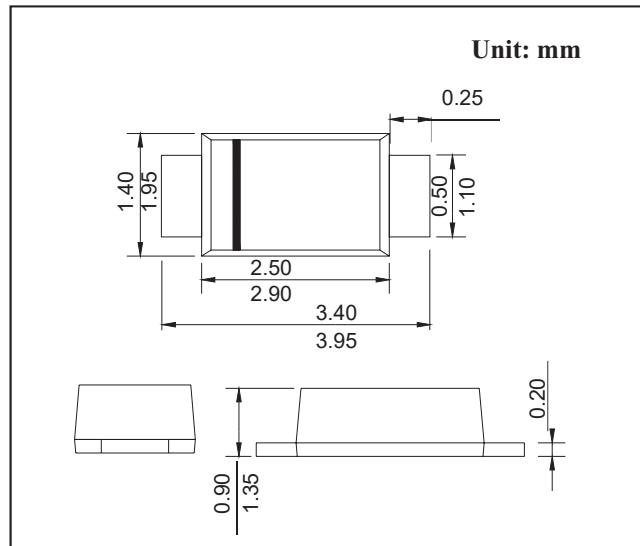
SOD123FL PLASTIC SILICON RECTIFIERS

FEATURES

- Glass passivated device
- Ideal for surface mounted applications
- Low reverse leakage
- Metallurgically bonded construction
- High temperature soldering guaranteed:
250 C/10 seconds, 0.375" (9.5mm) lead length,

MECHANICAL DATA

- Case : JEDEC SOD-123FL molded plastic bodyover
- passivated chip
- Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	SYMBOLS	F1A	F1B	F1D	F1G	F1J	F1K	F1M	UNITS
	MARK	F1A	F1B	F1D	F1G	F1J	F1K	F1M	
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at TA=65°C (NOTE 1)	I _(AV)	1.0						Amp	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) TL=25°C	I _{FSM}	30.0						Amps	
Maximum instantaneous forward voltage at 1.0A	V _F	1.3						Volts	
Maximum DC reverse current TA=25°C at rated DC blocking voltage TA=125°C	I _R	5.0 50.0						µA	
Maximum reverse recovery time (NOTE 2)	trr	150		250	500				ns
Typical junction capacitance (NOTE 3)	C _J	4						pF	
Typical thermal resistance (NOTE 4)	R _{θJA}	180						K/W	
Operating junction and storage temperature range	T _J T _{STG}	-55 to +150						°C	

Note: 1.Averaged over any 20ms period.

2. Measured with IF=0.5A, IR=1A, Irr=0.25A.

3.Measured at 1MHz and applied reverse voltage of 4.0V D.C.

4.Thermal resistance junction to ambient, 6.0 mm² copper pads to each terminal.

RATINGS AND CHARACTERISTIC CURVES

FIG.1 --TYPICAL FORWARD CHARACTERISTIC

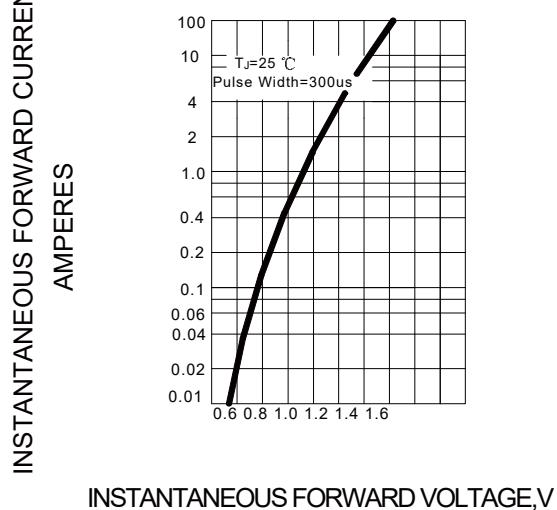


FIG.2 -- TYPICAL JUNCTION CAPACITANCE

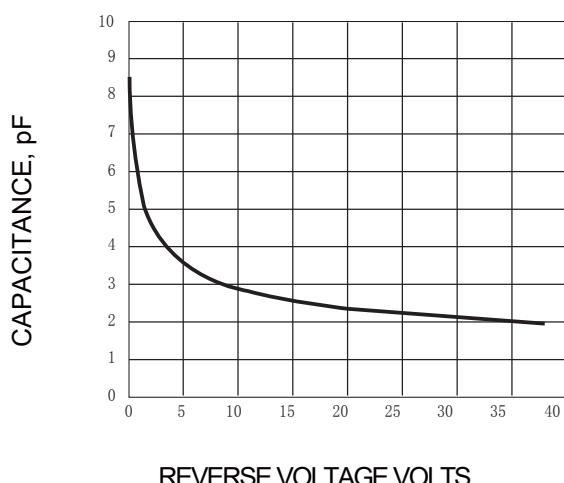


FIG.3 – TYPICAL INSTANTANEOUS REVERSE CHARACTERISTICS

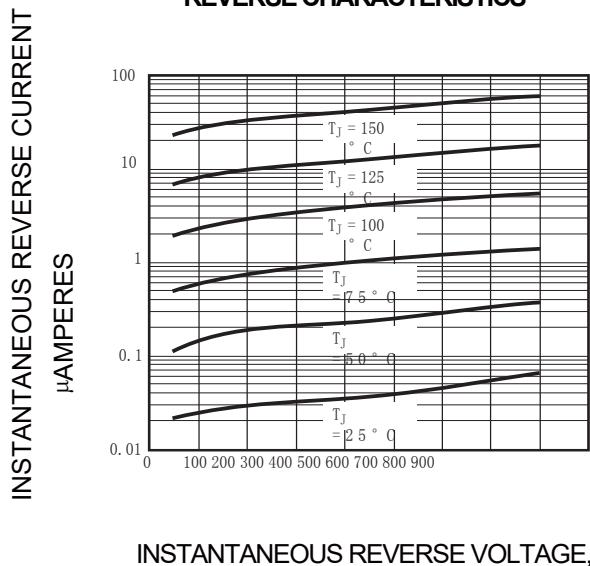


FIG.4 – FORWARD DERATING CURVE

